Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

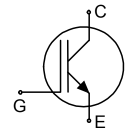
Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
  - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

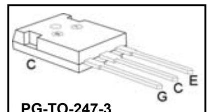
Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

Low Loss IGBT in TrenchStop® and Fieldstop technology



- Short circuit withstand time – 10µs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 1200 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/



PG-TO-247-3

Type	V_{CE}	I_C	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking	Package
IGW25T120	1200V	25A	1.7V	150°C	G25T120	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current T_C = 25°C T_C = 100°C	I_C	 50 25	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	75	
Turn off safe operating area $V_{CE} \leq$ 1200V, $T_j \leq$ 150°C	-	75	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)] V_{GE} = 15V, $V_{CC} \leq$ 1200V, $T_j \leq$ 150°C	t_{SC}	10	µs
Power dissipation T_C = 25°C	P_{tot}	190	W
Operating junction temperature	T_j	-40...+150	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

[1] J-STD-020 and JESD-022

[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.65	K/W
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=500µA	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=25A				
		T_j=25°C	-	1.7	2.2	
		T_j=125°C	-	2.0	-	
		T_j=150°C	-	2.2	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=1mA, V_{CE}=V_{GE}	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	V_{CE}=1200V, V_{GE}=0V				mA
		T_j=25°C	-	-	0.25	
		T_j=150°C	-	-	2.5	
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	600	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=25A	-	16	-	S
Integrated gate resistor	R_{Gint}			8		Ω

Dynamic Characteristic

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Input capacitance	C_{iss}	V_{CE}=25V,	-	1860	-	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	96	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	82	-	
Gate charge	Q_{Gate}	V_{CC}=960V, I_C=25A V_{GE}=15V	-	155	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH
Short circuit collector current[1]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤10µs V_{CC} = 600V, T_j = 25°C	-	150	-	A

[1] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=600V, I_C=25A V_{GE}=-15/15V, R_G=22Ω, L_σ[2)]=180nH, C_σ[2)]=39pF Energy losses include "tail" and diode reverse recovery.	-	50	-	ns
Rise time	t_r		-	30	-	
Turn-off delay time	$t_{d(off)}$		-	560	-	
Fall time	t_f		-	70	-	
Turn-on energy	E_{on}		-	2.0	-	mJ
Turn-off energy	E_{off}		-	2.2	-	
Total switching energy	E_{ts}		-	4.2	-	

Switching Characteristic, Inductive Load, at T_j=150 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=150°C V_{CC}=600V, I_C=25A, V_{GE}=-15/15V, R_G= 22Ω, L_σ[2)]=180nH, C_σ[2)]=39pF Energy losses include "tail" and diode reverse recovery.	-	50	-	ns
Rise time	t_r		-	32	-	
Turn-off delay time	$t_{d(off)}$		-	660	-	
Fall time	t_f		-	130	-	
Turn-on energy	E_{on}		-	3.0	-	mJ
Turn-off energy	E_{off}		-	4.0	-	
Total switching energy	E_{ts}		-	7.0	-	

[2)] Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.

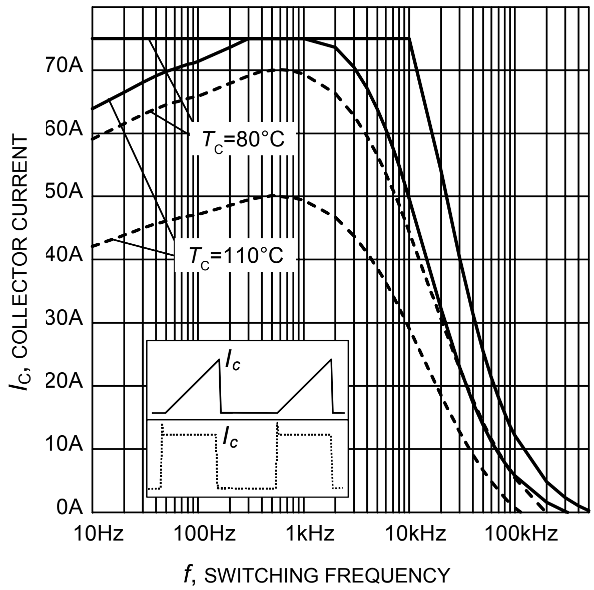


Figure 1. Collector current as a function of switching frequency
($T_j \leq 150°C$, $D = 0.5$, $V_{CE} = 600V$, $V_{GE} = 0/+15V$, $R_G = 22\Omega$)

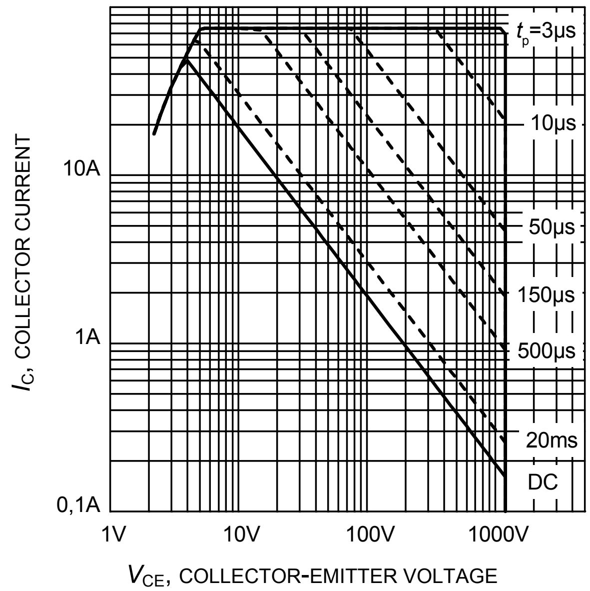


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 150°C$; V_{GE}=15V)

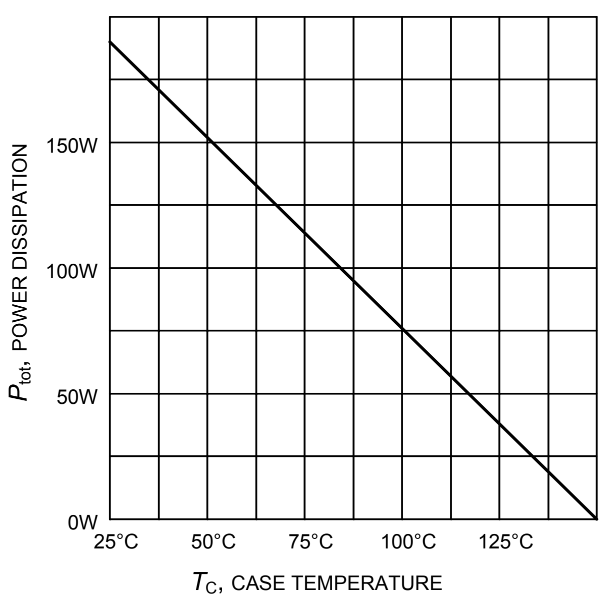


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 150°C$)

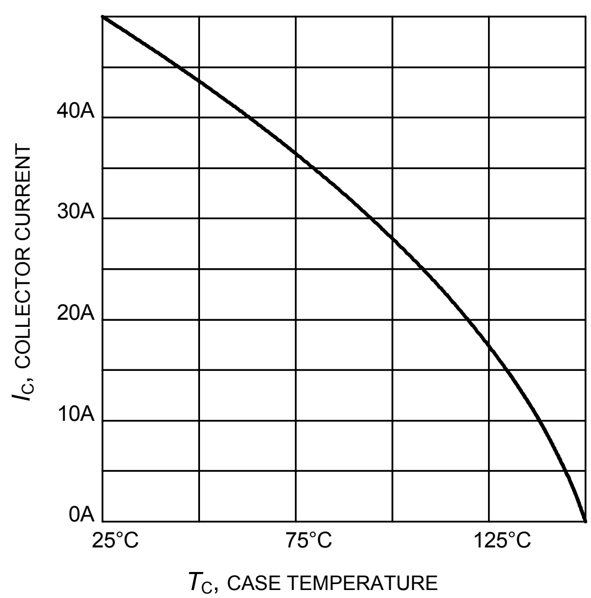


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15V$, $T_j \leq 150°C$)

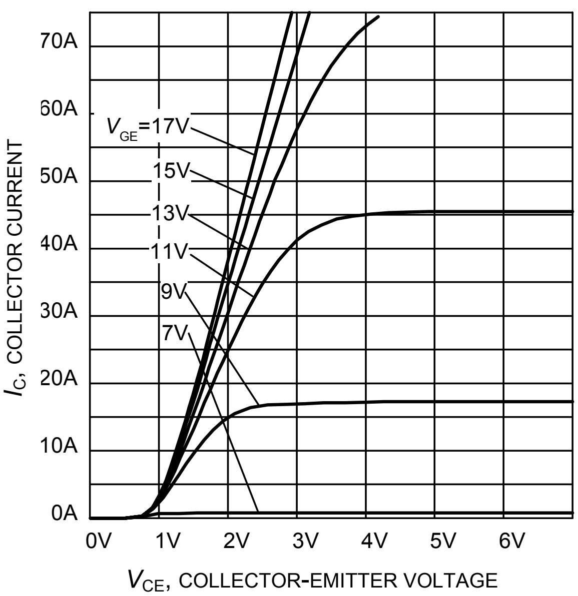


Figure 5. Typical output characteristic
(T_j = 25°C)

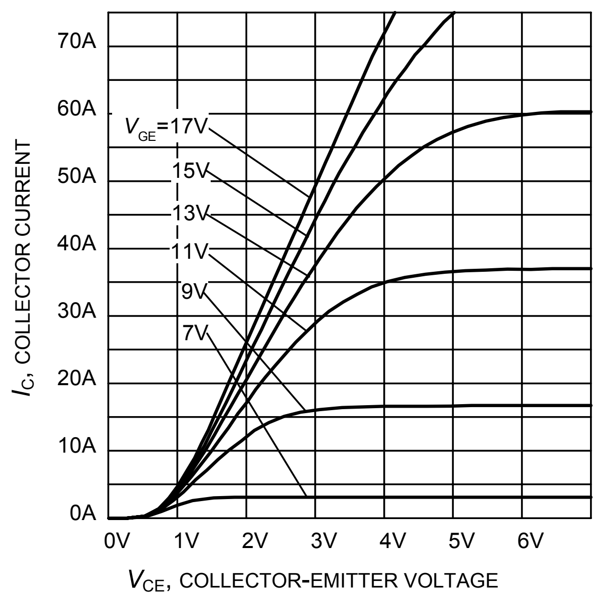


Figure 6. Typical output characteristic
(T_j = 150°C)

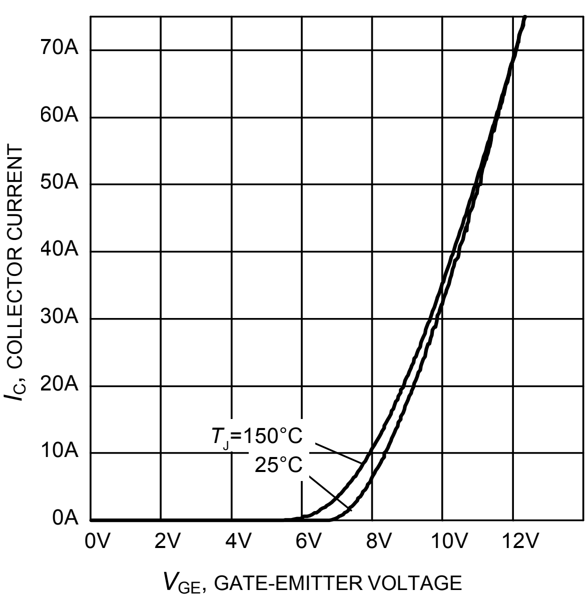


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

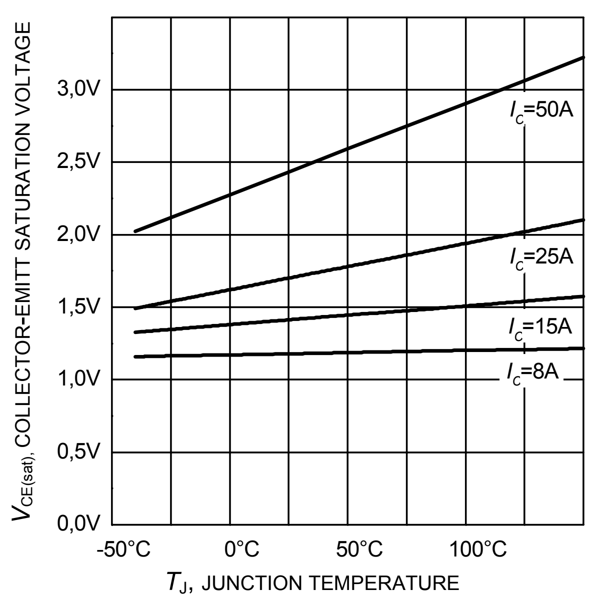


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

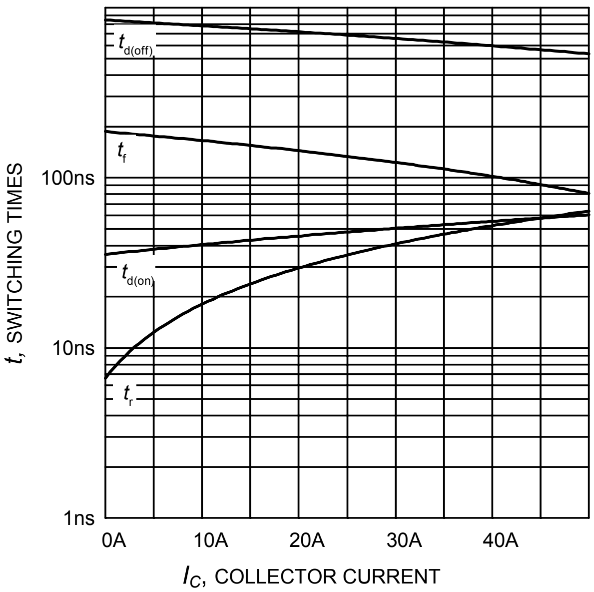


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=150°C, V_{CE}=600V, V_{GE}=0/15V, R_G=22Ω, Dynamic test circuit in Figure E)

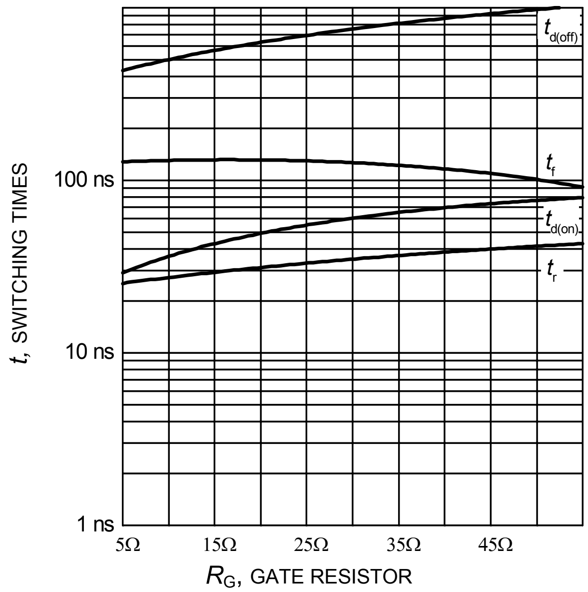


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J=150°C, V_{CE}=600V, V_{GE}=0/15V, I_C=25A, Dynamic test circuit in Figure E)

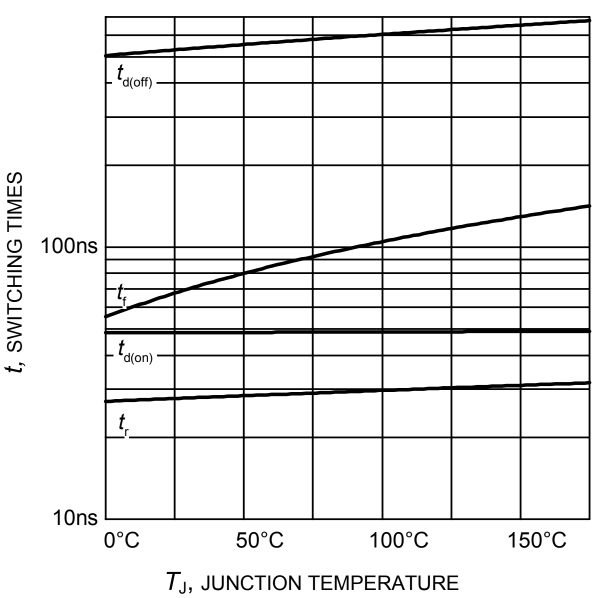


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=25A, R_G=22Ω, Dynamic test circuit in Figure E)

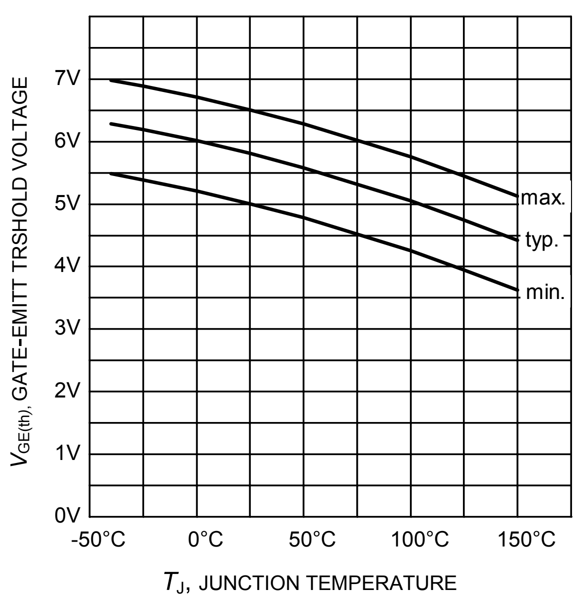


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 1.0mA)

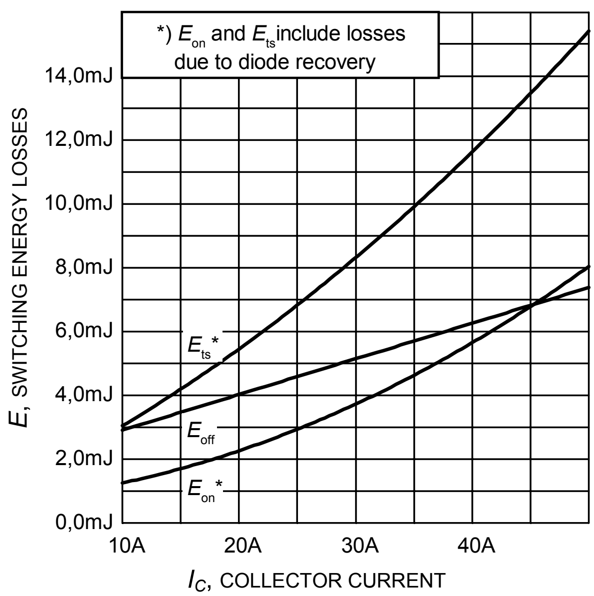


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J=150°C, V_{CE}=600V, V_{GE}=0/15V, R_G=22Ω, Dynamic test circuit in Figure E)

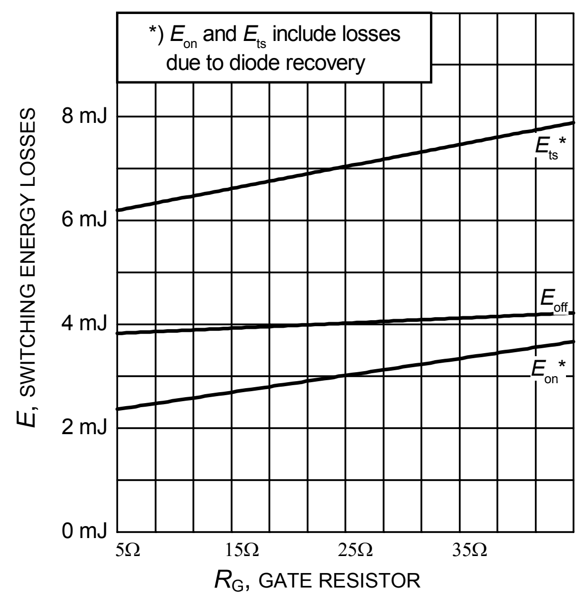


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J=150°C, V_{CE}=600V, V_{GE}=0/15V, I_C=25A, Dynamic test circuit in Figure E)

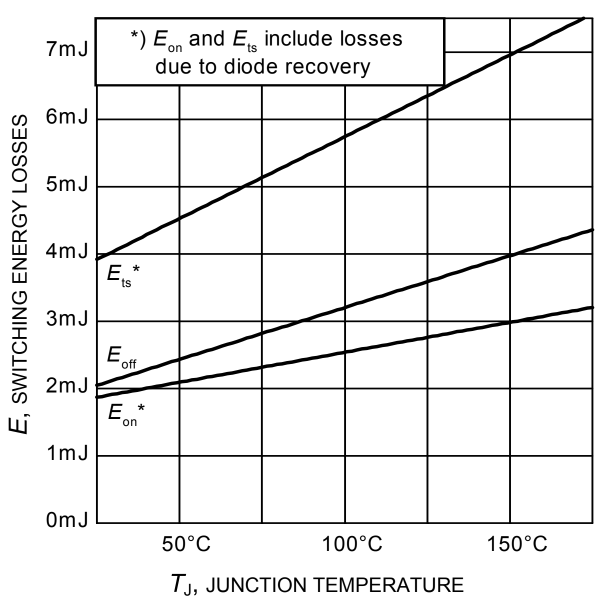


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=25A, R_G=22Ω, Dynamic test circuit in Figure E)

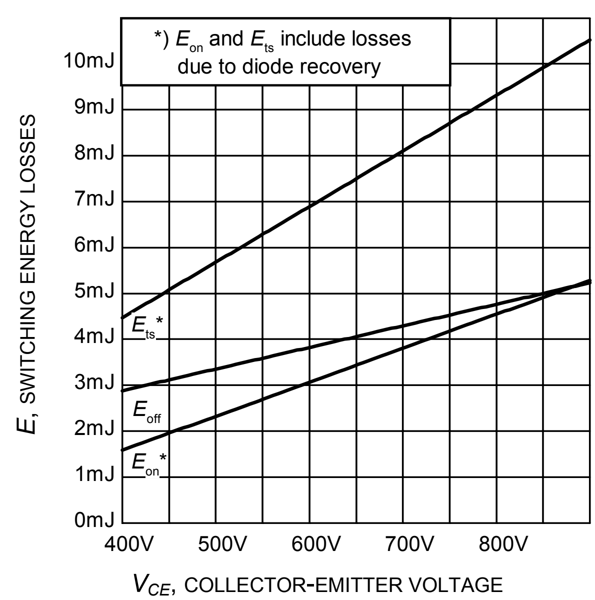


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J=150°C, V_{GE}=0/15V, I_C=25A, R_G=22Ω, Dynamic test circuit in Figure E)

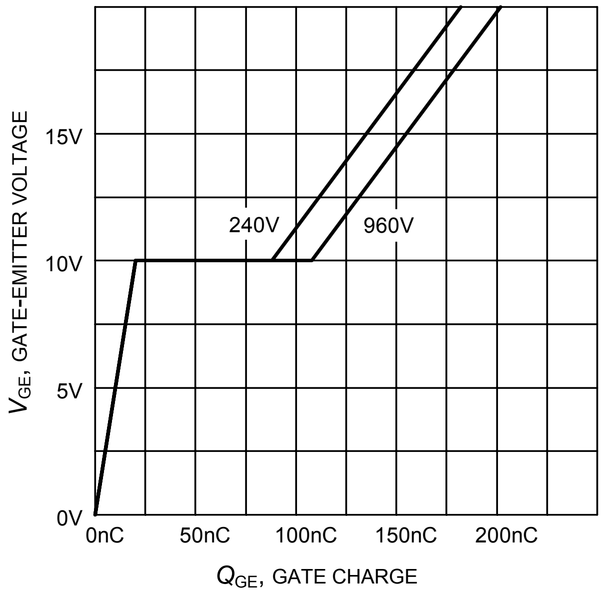


Figure 17. Typical gate charge
(I_C=25 A)

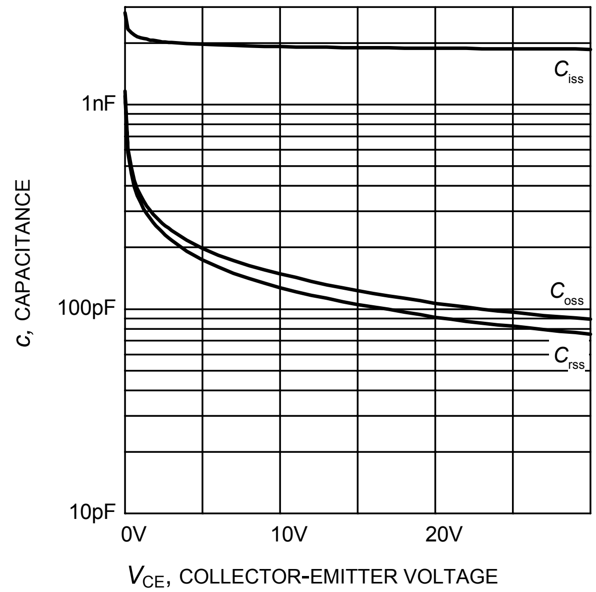


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

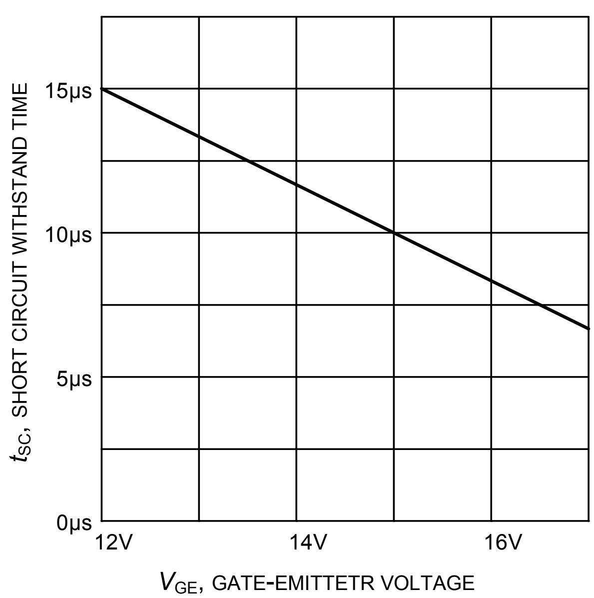


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=600V, start at T_J=25°C)

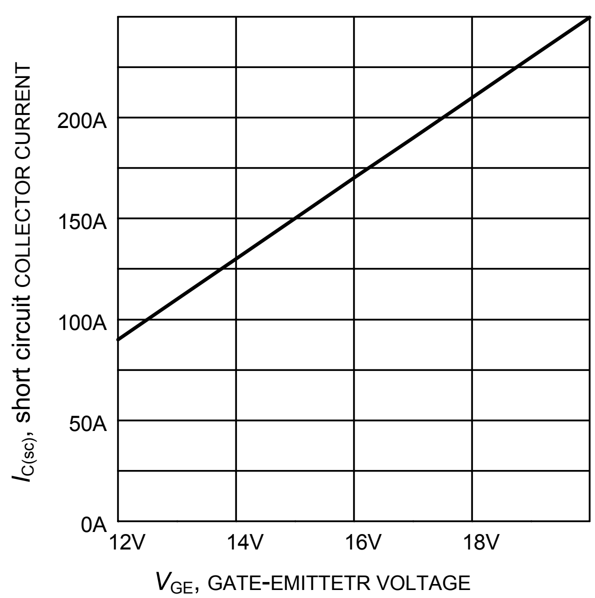


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600V$, $T_j \leq 150°C$)

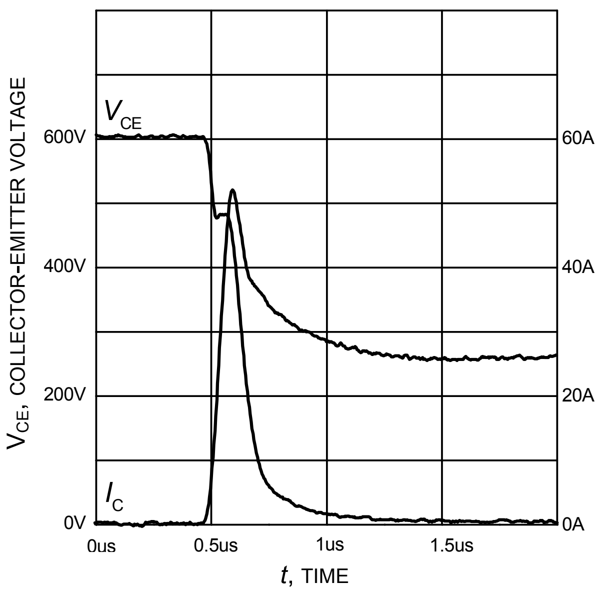


Figure 21. Typical turn on behavior
(V_{GE}=0/15V, R_G=22Ω, T_j = 150°C, Dynamic test circuit in Figure E)

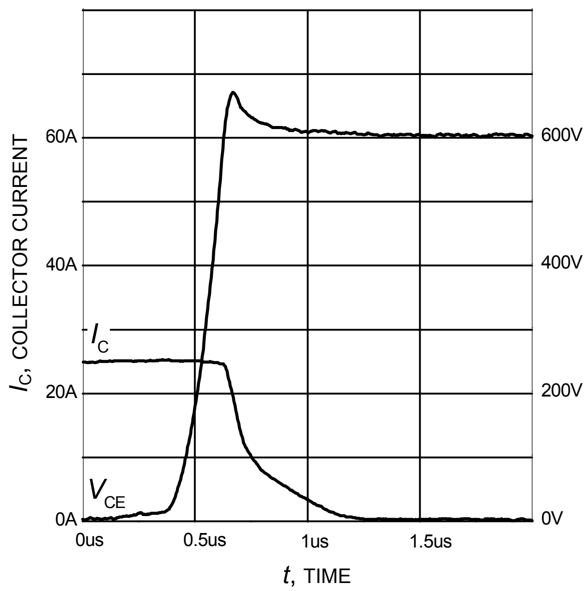


Figure 22. Typical turn off behavior
(V_{GE}=15/0V, R_G=22Ω, T_j = 150°C, Dynamic test circuit in Figure E)

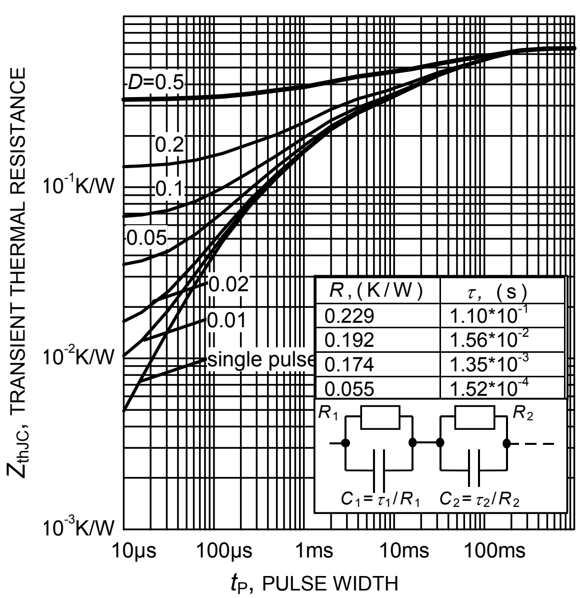


Figure 23. IGBT transient thermal resistance
($D = t_p / T$)

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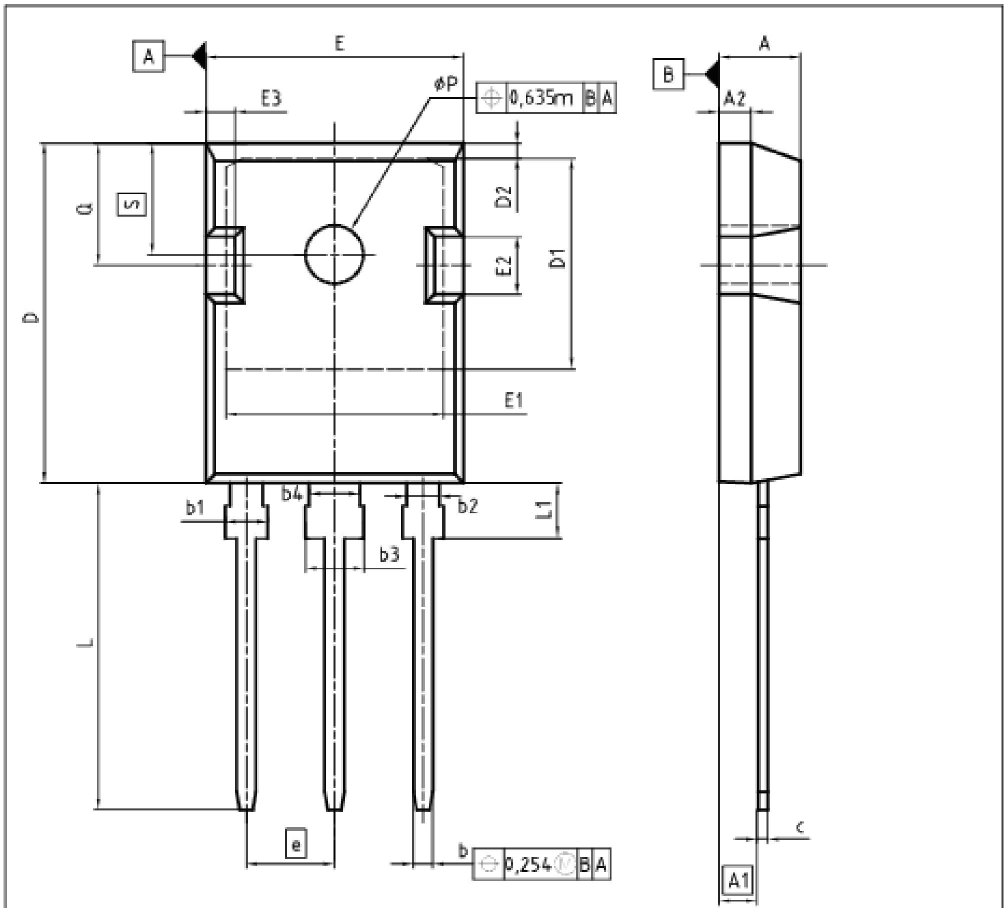

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0 5 7.5mm

EUROPEAN PROJECTION

ISSUE DATE
01-10-2009

REVISION
04

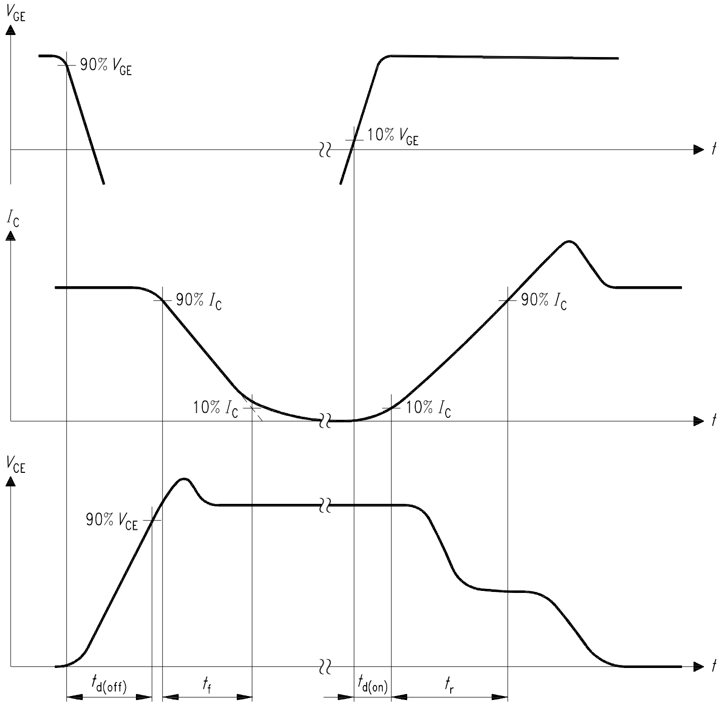

Figure A. Definition of switching times

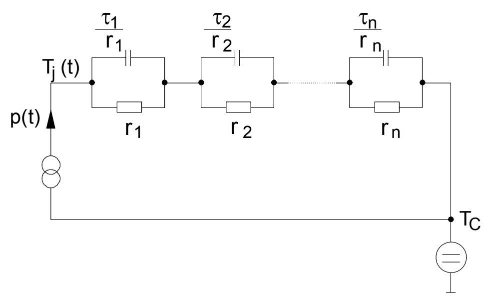

Figure D. Thermal equivalent circuit

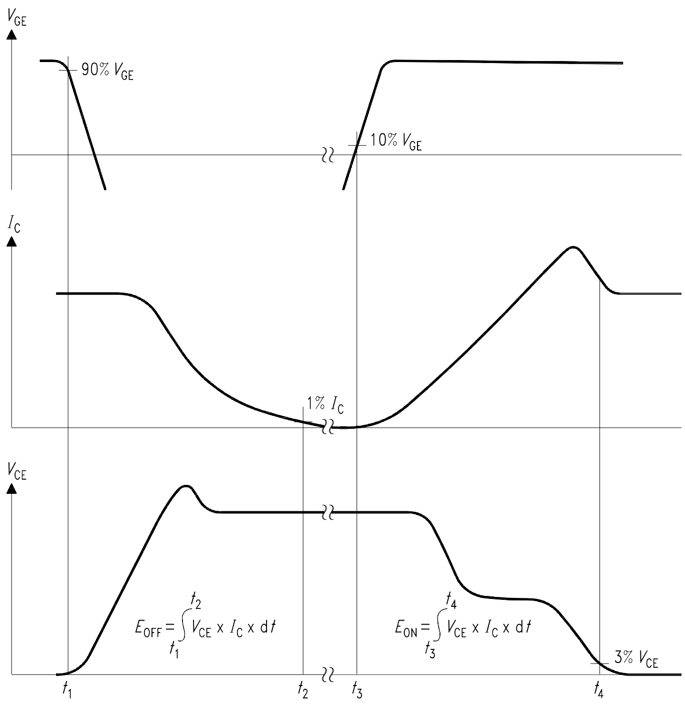

Figure B. Definition of switching losses

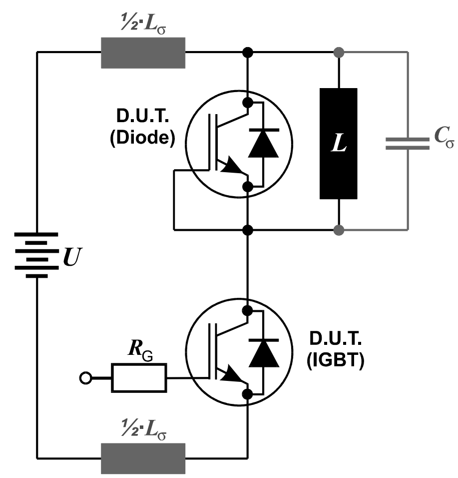

Figure E. Dynamic test circuit
Leakage inductance L_σ =180nH
and Stray capacity C_σ =39pF.

Edition 2006-01

Published by
Infineon Technologies AG
81726 München, Germany

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